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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

**Examiner
Signature**

Date
Considered

3/18/07

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This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete. Including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

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Substitute for form 1449B/1-10

(use as many sheets as necessary)

Sheet 2

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Complete if Known

Application Number	10/720,035
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Filing Date	11/21/2003
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First Named Inventor	Juergens, Tristan Dieter
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Art Unit	Unknown
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Examiner Name	Unknown
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Attorney Docket Number	35811-00001
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**Examiner
Signature**

Date
Considered

3/18/07

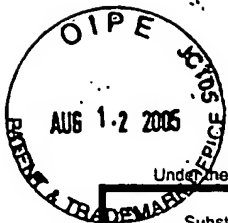
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PTO/SB/08a (08-03)

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		Complete if Known			
		Application Number	10/720,035		
		Filing Date	11/21/2003		
		First Named Inventor	Tsang et al.		
		Art Unit	3641		
		Examiner Name	Daniel L. Greene, Jr.		
Sheet	1	of	2	Attorney Docket Number	35811_00001

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
<i>[Handwritten initials]</i>	7	US-5,087,533 A	02-11-1992	Brown	
	8	US-6,118,204 A	09-12-2000	Brown	
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FOREIGN PATENT DOCUMENTS						
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		Country Code ³ - Number ⁴ - Kind Code ⁵ (if known)				

Examiner Signature	<i>[Handwritten Signature]</i>	Date Considered	3/18/07
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Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>				Complete if Known	
				Application Number	10/720,035
				Filing Date	11/21/2003
				First Named Inventor	Tsang et al.
				Art Unit	3641
				Examiner Name	Daniel L. Greene, Jr.
				Attorney Docket Number	35811_00001

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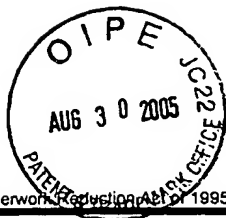
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This collection of information is required by 37 CFR 1.87 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

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		Application Number	10/720,035
		Filing Date	11/21/2003
		First Named Inventor	Tsang et al.
		Art Unit	3641
		Examiner Name	Daniel L. Greene, Jr.
Sheet	1	of	1
		Attorney Docket Number	35811_00001

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		Number - Kind Code ² (if known)			
[Signature]	11	US-5,721,462 A	02-24-1998	Shanks	
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Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ - Number ⁴ - Kind Code ⁵ (if known)				

Examiner Signature	[Signature]	Date Considered	3/18/07
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Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

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Complete if Known

Application Number	10/720,035
Filing Date	November 21, 2003
First Named Inventor	Tsang, Francis
Group Art Unit	3663
Examiner Name	Unknown

Sheet 1 of 4

Attorney Docket No: 2408.001US1

US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Filing Date If Appropriate
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<i>[Handwritten]</i>	US-4,259,419	03/31/1981	Uba, Toshio, et al.	08/17/1979
<i>[Handwritten]</i>	US-4,493,221	01/15/1985	Stieg, Richard f., et al.	01/12/1983
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<i>[Handwritten]</i>	US-4,606,982	08/19/1986	Nelson, Robert F., et al.	05/09/1985
<i>[Handwritten]</i>	US-5,045,086	09/03/1991	Juergens, Tristan	09/27/1989
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<i>[Handwritten]</i>	US-5,677,078	10/14/1997	Juergens, Tristan, et al.	09/27/1995
<i>[Handwritten]</i>	US-5,895,728	04/20/1999	Walker, Thomas P., et al.	01/15/1997
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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
<i>[Handwritten]</i>		"4-pocket Electron Bean Evaporator", e-flux4, tec tra, 5 Pages	
<i>[Handwritten]</i>		"Annealing (Metallurgy)", Wikipedia, http://en.wikipedia.org/wiki/Annealing_%28metallurgy%29 , 1 Page	
<i>[Handwritten]</i>		"Carbon Coaters, Sputter Coaters and Turbo Sputter Coaters", <u>Electron Microscopy Sciences</u> , http://www.emsdiasum.com/microscopy/products/equipment/carbon_coaters.aspx , 8 Pages	
<i>[Handwritten]</i>		"E-beam Evaporator", <u>Brigham Young University, Department of Electrical & Computer Engineering</u> , http://www.ee.byu.edu/cleanroom/ebeam.phtml , (Observed 11/7/06), 2 Pages	
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<i>[Handwritten]</i>		"Sputter-Coater high vacuum coating system for thin film deposition", http://www.tecra.de/spuco.htm , (Observed 11/7/06), 5 Pages	
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Substitute Disclosure Statement Form (PTO-1449)

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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

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Complete if Known

Application Number 10/720,035

Filing Date November 21, 2003

First Named Inventor Tsang, Francis

Group Art Unit 3663

Examiner Name Unknown

Sheet 2 of 4

Attorney Docket No: 2408.001US1

OTHER DOCUMENTS – NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
<i>del</i>		BRILLSON, LEONARD J., "Contacts to Semiconductors", <u>Contacts to Semiconductors, Fundamentals and Technology</u> , Xerox Corporation, Noyes Publications, New Jersey, (1993)	
<i>del</i>		BULLOCK, ALAN, et al., "The Harper Dictionary of Modern Thought", <u>The Harper Dictionary of Modern Thought</u> , Harper & Row, New York, (1977), Page 25	
<i>del</i>		CONSIDINE, GLENN D., <u>Encyclopedia of Chemistry</u> , Fifth Edition, Van Nostrand's, John Wiley & Sons, Inc., (2005)	
<i>del</i>		CUTLER, MELVIN, "Experimental Methods", <u>Chapter 4, Liquid Semiconductors</u> , Academic Press Inc., (1977), 7 Pages	
<i>del</i>		[REDACTED]	
<i>del</i>		FARRELL, MARTIN V., et al., "Coupling of Buoyant Convections in Boron Oxide and a Molten Semiconductor in a Ventical Magnetic Field", <u>Journal of Heat Transfer</u> , Vol. 124, (August 2002), 643-649	
<i>del</i>		GEARHART, STEVEN S., et al., "A Monolithic 250 GHz Schottky-Diode Receiver", <u>IEEE Transactions on Microwave Theory and Techniques</u> , Vol. 42, No. 12, (December 1994), 2504-2511	
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<i>del</i>		HARRELL, WILLIAM R., "Aluminum schottky contacts to n-type 4H-SiC", <u>Look Smart</u> , http://findarticles.com/p/articles/mi_qa3776/is_200210/ai_n9137011 , (October 2002), 4 pages	
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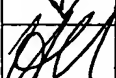
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Filing Date	November 21, 2003
First Named Inventor	Tsang, Francis
Group Art Unit	3663
Examiner Name	Unknown

Sheet 3 of 4

Attorney Docket No: 2408.001US1

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

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		KNOLL, GLENN F., "Radiation Detection and Measurement", <u>Radiation Detection and Measurement</u> , Third Edition, John Wiley & Sons, Inc., New York, (2000)	
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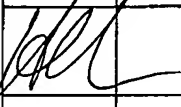
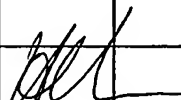
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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Complete if Known	
	Application Number	10/720,035
	Filing Date	November 21, 2003
	First Named Inventor	Tsang, Francis
	Group Art Unit	3663
	Examiner Name	Unknown
Sheet 4 of 4	Attorney Docket No: 2408.001US1	

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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<i>[Signature]</i>		ENDERBY, J. E., "Liquid semiconductors", Rep. Prog. Phys., 53, (1990), 85-179	

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